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Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

#### NPN SILICON DUAL TRANSISTOR Qualified per MIL-PRF-19500 /355

DEVICES	2N2919 2N2919L 2N2920 2N2920L		919U 920U			LEVELS JAN JANTX JANTV JANS
ABSOLUTE	MAXIMUM RATINGS ( $T_C = +25^{\circ}$	C unless of	herwise note	<i>d</i> )		
Pa	rameters / Test Conditions	Symbol	Va	lue	Unit	$\frown$
Collector-Em	itter Voltage	V <sub>CEO</sub>	6	0	Vdc	$\widetilde{M}$
Collector-Base Voltage		V <sub>CBO</sub>	70		Vdc	
Emitter-Base Voltage		V <sub>EBO</sub>	6.0		Vdc	
Collector Current		I <sub>C</sub>	30		mAdc	
			One Section <sup>1</sup>	Both Sections <sup>2</sup>		
Total Power I	Dissipation (a) $T_A = +25^{\circ}C$	P <sub>T</sub>	200	350	mW	
Operating & Storage Junction Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-65 to	+200	°C	<b>TO-78</b>
2. Dera	te linearly 1.143mW/°C for $T_A > +25$ te linearly 2.000mW/°C for $T_A > +25$ <b>AL CHARACTERISTICS (</b> $T_A = +2$	5°C (both so	ections)	oted)		
Par	rameters / Test Conditions	Symbol	Min.	Max.	Unit	

V<sub>(BR)CEO</sub>

 $I_{CBO}$ 

 $I_{EBO}$ 

60

Vdc

ηAdc

μAdc

ηAdc

μAdc

2.0

10

2.0

10

**OFF CHARACTERTICS** 

Collector-Base Cutoff Current

Emitter-Base Cutoff Current

 $I_C = 10 \text{mAdc}$ ; Pulsed

 $V_{CB} = 45 V dc$ 

 $V_{CB} = 70 V dc$ 

 $V_{EB} = 5.0 V dc$ 

 $V_{EB} = 6.0 V dc$ 

Collector-Emitter Breakdown Voltage

U - Package



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# ELECTRICAL CHARACTERISTICS (con't)

Parameters / Test Conditions		Symbol	Min.	Max.	Unit
ON CHARACTERTICS					
Forward-Current Transfer Ratio $I_C = 10\mu Adc, V_{CE} = 5.0Vdc$ $I_C = 100\mu Adc, V_{CE} = 5.0Vdc$ $I_C = 1.0mAdc, V_{CE} = 5.0Vdc$	2N2919, 2N2919L , 2N2919U	$\mathbf{h}_{\mathrm{FE}}$	60 100 150	240 325 600	
$I_{C} = 10\mu Adc, V_{CE} = 5.0Vdc$ $I_{C} = 100\mu Adc, V_{CE} = 5.0Vdc$ $I_{C} = 1.0mAdc, V_{CE} = 5.0Vdc$	2N2920, 2N2920L, 2N2920U	$\mathbf{h}_{\mathrm{FE}}$	175 235 300	600 800 1000	
Collector-Emitter Saturation Voltage					
$I_{\rm C} = 1.0 \text{mAdc}, I_{\rm B} = 100 \mu \text{Adc}$		V <sub>CE(sat)</sub>		0.3	Vdc
Base-Emitter Saturation Voltage $I_C = 1.0$ mAdc, $I_B = 100\mu$ Adc		$V_{BE(sat)}$	0.5	1.0	Vdc

### **DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Forward Current Transfer Ratio, Magnitude $I_C = 0.5 \text{mAdc}, V_{CE} = 5.0 \text{Vdc}, f = 20 \text{MHz}$	h <sub>fe</sub>	3.0	20	
Small-Signal Short Circuit Input Impedance $I_C = 1.0$ mAdc, $V_{CE} = 5$ Vdc, $f = 1.0$ kHz	h <sub>je</sub>	3.0	30	kΩ
Small-Signal Short Circuit Output Admittance $I_C = 1.0$ mAdc, $V_{CE} = 5$ Vdc, $f = 1.0$ kHz	h <sub>oe</sub>		60	μmhos
Output Capacitance $V_{CB} = 5.0$ Vdc, $I_E = 0$ , 100kHz $\leq f \leq 1.0$ MHz	C <sub>obo</sub>		5.0	pF
Noise Figure				
$I_C = 10 \mu Adc$ , $V_{CE} = 5Vdc$ , $f = 100Hz$ , $R_G = 10k\Omega$	$F_1$		5.0	
$I_C = 10 \mu Adc$ , $V_{CE} = 5Vdc$ , $f = 1.0 kHz$ , $R_G = 10 k\Omega$	$F_2$		3.0	dB
$I_C = 10\mu Adc$ , $V_{CE} = 5Vdc$ , $f = 10kHz$ , $R_G = 10k\Omega$	F <sub>3</sub>		3.0	



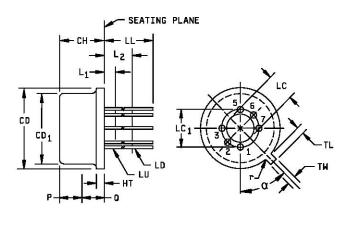
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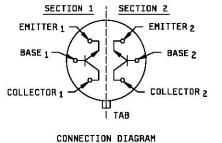
DIMENSIONS

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## **PACKAGE DIMENSIONS**





Symbol Inches		hes	Millimeters		Notes
	Min	Max	Min	Max	
CD	.335	.370	8.51	9.40	
CD1	.305	.335	7.75	8.51	
СН	.140	.260	3.56	6.60	
HT	.009	.041	0.23	1.04	
LC	.140	.160	3.56	4.06	
LC1	.200 TP		5.08	3 TP	9
LD	.016	.021	.041	0.53	10
LL		See no	tes 10, 11	and 12	
LU	.016	.019	.041	0.48	10
L1		.050		1.27	10
L2	.250		6.35		10
Р	.100		2.54		8
Q		.050		1.27	7
TL	.029	.045	0.74	1.14	5,6
TW	.028	.034	0.71	0.86	4, 5
r		.010		0.25	
α	45°TP		45°	PTP	9

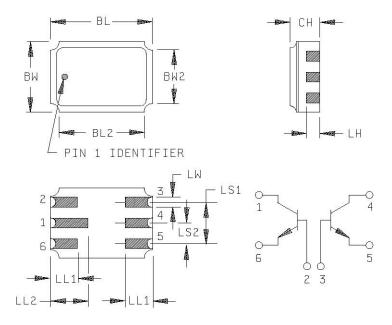
#### **NOTES:**

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- 3 Tab Shown omitted.
- 4 Lead number 4 and 8 omitted on this variation.
- 5 Beyond r maximum, TW shall be held to a minimum length of .21 inch (5.33 mm)
- 6 TL shall be measured from maximum CD.
- 7 Details of outline in this zone are optional.
- 8 CD1 shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 9 Leads at gauge plane .054 .055 inch (1.37 1.40 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at a maximum material condition (MMC) relative to the tab at MMC. The device may be measured by direct methods or by the gauge and gauging procedures described on gauge drawing GS-1.
- 10 LU applies between L1 and L2. LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 11 For transistor types 2N2919 and 2N2920, LL is .500 inch (12.70 mm) minimum and .750 inch (19.05 mm) maximum.
- 12 For transistor type 2N2919L and 2N2920L, LL is 1.500 inches (38.10 mm) minimum and 1.750 inches (44.45 mm) maximum.
- 13 In accordance with ASME Y14.5M, diameters are equivalent to  $\phi x$  symbology.

#### FIGURE 1. Physical dimensions 2N2919, 2N2919L, 2N2920, and 2N2920L (TO-78).



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	Dimensions					
Symbol	Inc	hes	Millimeters			
	Min	Max	Min	Max		
BL	.240	.250	6.10	6.35		
BL2		.250		6.35		
BW	.165	.175	4.19	4.44		
BW2		.175		4.44		
СН	.044	.080	1.12	2.03		
LH	.026	.039	0.66	0.99		
LL1	.060	.070	1.52	1.78		
LL2	.082	.098	2.08	2.49		
LS1	.095	.105	2.41	2.67		
LS2	.045	.055	1.14	1.39		
LW	.022	.028	0.56	0.71		

Pin no.	Transistor
1	Collector no. 1
2	Base no. 1
3	Base no. 2
4	Collector no. 2
5	Emitter no. 2
6	Emitter no. 1

# NOTES:

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- 3 In accordance with AMSE Y14.5M, diameters are equivalent to \$\phi\$x symbology.

FIGURE 2. Physical dimensions (2N2919U and 2N2920U) Surface mount.

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